

Piotr Boguslawski

List of Publications by Year in descending order

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46

papers

1,803

citations

471061

17

h-index

288905

40

g-index

46

all docs

46

docs citations

46

times ranked

1735

citing authors

#	ARTICLE	IF	CITATIONS
1	Topological Phase Diagram of Semimagnetic Semiconductor Pb _{1-x-y} Sn _x Mn _y Te. <i>Acta Physica Polonica A</i> , 2022, 141, 156-160.	0.2	0
2	Band structure and topological phases of $\text{Pb}_{1-x-y}\text{Sn}_x\text{Mn}_y\text{Te}$ by ab initio calculations. <i>Physical Review B</i> , 2021, 103, .		
3	Calculated optical properties of Co in ZnO: internal and ionization transitions. <i>Journal of Physics Condensed Matter</i> , 2019, 31, 255501.	0.7	4
4	Green luminescence and calculated optical properties of Cu ions in ZnO. <i>Journal of Alloys and Compounds</i> , 2019, 782, 1024-1030.	2.8	6
5	Transition metal ions in ZnO: Effects of intrashell coulomb repulsion on electronic properties. <i>Optical Materials</i> , 2018, 79, 264-268.	1.7	5
6	Alloy broadening of the transition to the nontrivial topological phase of $\text{Pb}_{1-x-y}\text{Sn}_x\text{Mn}_y\text{Te}$. <i>Physical Review B</i> , 2018, 98, .		
7	Fe dopant in ZnO: 2+ versus 3+ valency and ion-carrier exchange interaction. <i>Physical Review B</i> , 2016, 94, .		
8	Metastability of Mn3+ in ZnO driven by strong d (Mn) intrashell Coulomb repulsion: Experiment and theory. <i>Physical Review B</i> , 2016, 94, .	1.1	10
9	Magnetic anisotropy energy in disordered Ge _{1-x-y} Mn _x Te. <i>Journal of Magnetism and Magnetic Materials</i> , 2016, 401, 788-795.		
10	Transition Metal Ions in Semiconductors: LDA, LDA+U, and Experiment. <i>Acta Physica Polonica A</i> , 2015, 127, 321-323.	0.2	4
11	DFT calculations of magnetic anisotropy energy of Ge _{1-x-y} Mn _x Te ferromagnetic semiconductor. <i>Journal of Physics Condensed Matter</i> , 2015, 27, 226002.	0.7	6
12	Magnetic Anisotropy in GeMnTe - ab initio Calculations. <i>Acta Physica Polonica A</i> , 2014, 126, 1177-1179.	0.2	3
13	Impact of Exchange-Correlations Effects (+U Corrections) on the Energy Levels of Mn and Fe Impurities in GaN and AlN: A Comparison with Experiment. <i>Acta Physica Polonica A</i> , 2013, 124, 898-900.	0.2	1
14	Theory of nitrogen doping of carbon nanoribbons: Edge effects. <i>Journal of Chemical Physics</i> , 2012, 136, 014702.	1.2	26
15	Calculated electronic structure of Pb _{1-x-y} Sn _x Mn _y Te. <i>Journal of Chemical Physics</i> , 2011, 134, 114701.		
16	Influence of the electrical conductivity on magnetic properties of CdZnMnTe epitaxial layers. , 2010, , .		0
17	Theoretical Approach to Polarization Effects in Semiconductors. , 2008, , 2-25.		0
18	Towards efficient p-type doping of ZnO with group-V atoms: N versus As and Sb. <i>AIP Conference Proceedings</i> , 2007, , .	0.3	1

#	ARTICLE	IF	CITATIONS
19	Magnetic and structural properties of III V nitrides. <i>Physical Review B</i> , 2007, 75, .	1.1	86
20	Magnetism of CaAs, CaP, and CaN half-metals. <i>Journal of Alloys and Compounds</i> , 2006, 423, 191-193.	2.8	51
21	Properties of p-Type ZnO Grown by Oxidation of Zn-Group-V Compounds. <i>Materials Research Society Symposia Proceedings</i> , 2006, 957, 1.	0.1	1
22	Properties of wurtzite w-MnN and of w-MnN inclusions in (Ga,Mn)N. <i>Applied Physics Letters</i> , 2006, 88, 092502.	1.5	7
23	Interfacial Segregation and Electrodiffusion of Dopants in AlN/GaN Superlattices. <i>Physical Review Letters</i> , 2006, 96, 185501.	2.9	10
24	Theory of Electronic Structure and Magnetic Interactions in (Ga,Mn)N and (Ga,Mn)As. <i>AIP Conference Proceedings</i> , 2005, .	0.3	0
25	Fermi-level effects on the electronic structure and magnetic couplings in (Ga,Mn)N. <i>Physical Review B</i> , 2005, 72, .	1.1	28
26	Mn Interstitial Diffusion in(Ga,Mn)As. <i>Physical Review Letters</i> , 2004, 92, 037201.	2.9	476
27	Structural Properties of MnTe, ZnTe, and ZnMnTe. <i>Acta Physica Polonica A</i> , 2004, 106, 233-238.	0.2	33
28	Elastic Properties of Zinc Blende MnTe. <i>Acta Physica Polonica A</i> , 2004, 106, 239-247.	0.2	13
29	Surface Segregation of Ge at SiGe(001) by Concerted Exchange Pathways. <i>Physical Review Letters</i> , 2002, 88, 166101.	2.9	30
30	Electronic Structure and Optical Properties of GaAs _{1-x} N _x and Ga _{1-x} B _x As Alloys. <i>Acta Physica Polonica A</i> , 2002, 102, 633-641.	0.2	4
31	GaAs:N vs GaAs:B alloys: Symmetry-induced effects. <i>Physical Review B</i> , 2001, 64, .	1.1	68
32	Surface segregation and interface stability of AlN/GaN, GaN/InN, and AlN/InN {0001} epitaxial systems. <i>Physical Review B</i> , 2000, 61, 10820-10826.	1.1	26
33	Segregation effects at vacancies inAl _x Gal _{1-x} N and Si _x Ge _{1-x} alloys. <i>Physical Review B</i> , 1999, 59, 1567-1570.	1.1	16
34	Doping properties of C, Si, and Ge impurities in GaN and AlN. <i>Physical Review B</i> , 1997, 56, 9496-9505.	1.1	233
35	Ab Initio Studies of the Diffusion Barriers at Single-Height Si(100) Steps. <i>Physical Review Letters</i> , 1995, 75, 101-104.	2.9	107
36	Towards the Identification of the Dominant Donor in GaN. <i>Physical Review Letters</i> , 1995, 75, 296-299.	2.9	295

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37	Structure of monatomic steps on the Si(001) surface. Physical Review Letters, 1994, 72, 3694-3697.	2.9	56
38	Influence of Chemistry on the Energy Band Structure: AlAs Versus GaAs. Acta Physica Polonica A, 1991, 80, 433-436.	0.2	6
39	Surface Stability of Ordered $\text{Ga}_{0.5}\text{In}_{0.5}\text{P}$ and $\text{GaAs}_{0.5}\text{Sb}_{0.5}$ Alloys. Acta Physica Polonica A, 1991, 79, 125-128.	0.2	0
40	Thermodynamic Stability of Two Rhombohedral Phases of $\text{Si}_{0.5}\text{Ge}_{0.5}$ Alloy. Acta Physica Polonica A, 1991, 80, 299-302.	0.2	0
41	Optical-gap reduction in the ordered phases of GaInAs solid solution. Solid State Communications, 1989, 70, 1085-1090.	0.9	10
42	Excess elastic energy and the instability of $(\text{GaAs})_1(\text{InAs})_1(0\ 0\ 1)$, Ga_3InAs_4 , GaIn_3As_4 and $\text{Ga}_{1-x}\text{In}_x\text{As}$ alloys. Solid State Communications, 1988, 66, 679-682.	0.9	27
43	Ionicity-dependent structural properties of zinc-blende semiconductors. Solid State Communications, 1986, 57, 623-626.	0.9	7
44	The Theory of the Electron Spin-Lattice Relaxation in Zincblende Semiconductors. Physica Status Solidi (B): Basic Research, 1981, 104, 89-95.	0.7	1
45	Nonpolar Scattering of Electrons by Optical Phonons in Small-Gap Semiconductors. Physica Status Solidi (B): Basic Research, 1975, 70, 53-62.	0.7	24
46	Elastic Electron Scattering in Symmetry-Induced Zero-Gap Semiconductors. Physica Status Solidi (B): Basic Research, 1974, 65, 641-654.	0.7	54